

A Novel Ultra-High-Speed Sensor Implementation with Variable Spatial and Temporal Resolution using Temporal Pixel Multiplexing

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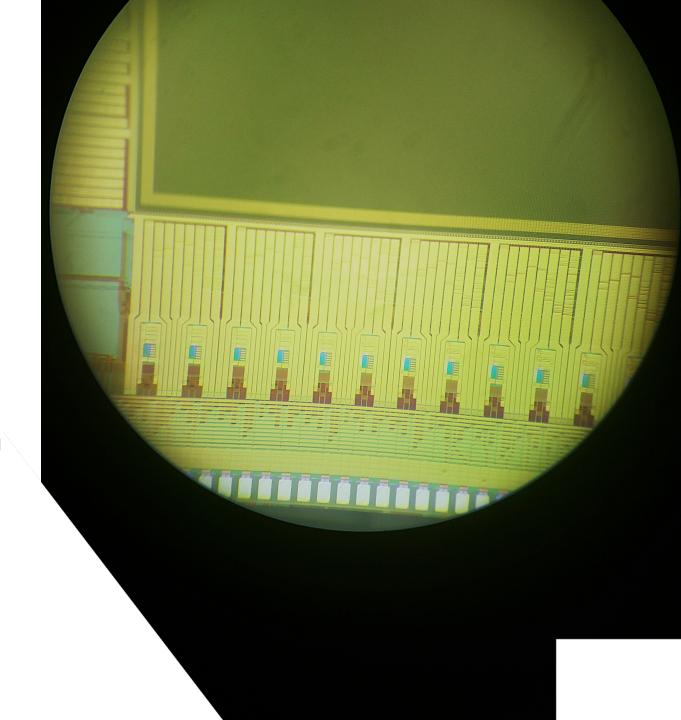
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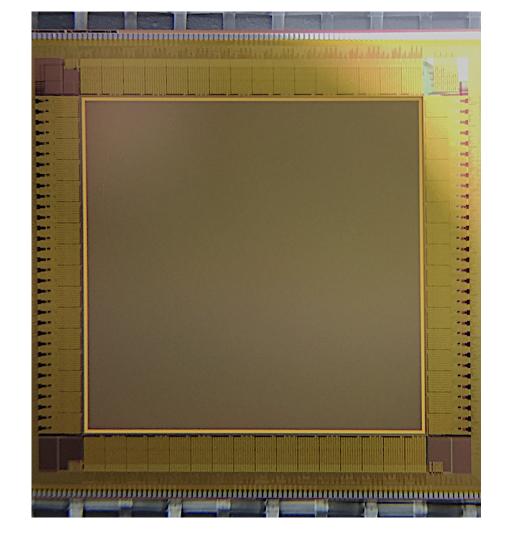


Primary application

High-Speed High-Resolution Optical Microscopy

The TPM CMOS sensor enables simultaneous high-speed imaging of cellular activity and high-spatial resolution imaging of anatomical structures.

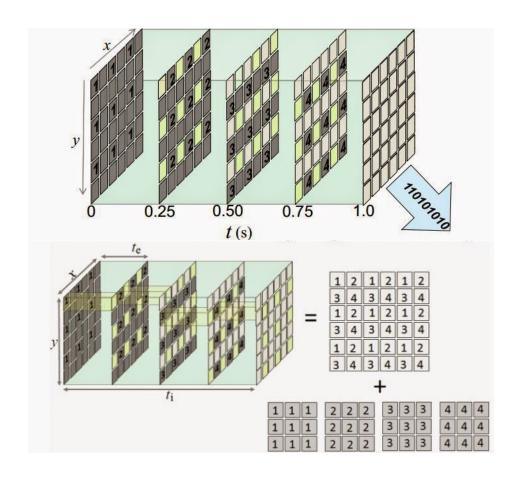
- Pixel pitch: 10 μm × 10 μm
- Frame rate: up to 10 Mfps
- Pixel array format: 1024 × 1024
- Configurable number of frames
- Analogue readout





TPM concept

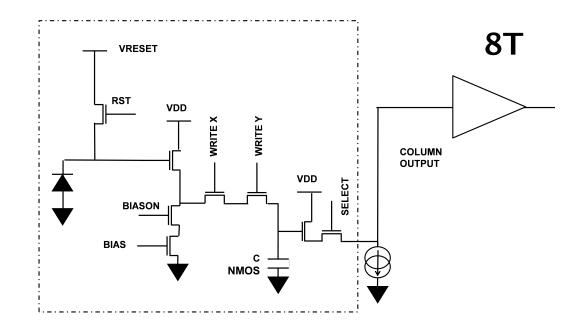
- Pixel array is arranged in a pre-specified grid pattern, e.g. a 2 × 2 grid pattern, as shown in figure on the right side of this slide.
- Each pixel with the same ID integrates light at the same time.
- Exposures of the resulting pixel groups are staggered throughout the detector's total exposure time.
- The full resolution frame is read out and digitized after all the pixel groups have finished integrating light.
- It can then be post-processed into a short movie, formed from lower resolution frames, consisting of pixels which have been exposed at the same time and collected together.
- In the example shown in this slide, 4 sequential 9-pixel subframes can be extracted from a single 36-pixel frame as follows:
 - The 1st subframe consisting of all pixels with ID #1;
 - The 2nd subframe consisting of all pixels with ID #2;
 - The 3rd subframe consisting of all pixels with ID #3;
 - The 4th subframe consisting of all pixels with ID #4.





TPM pixel

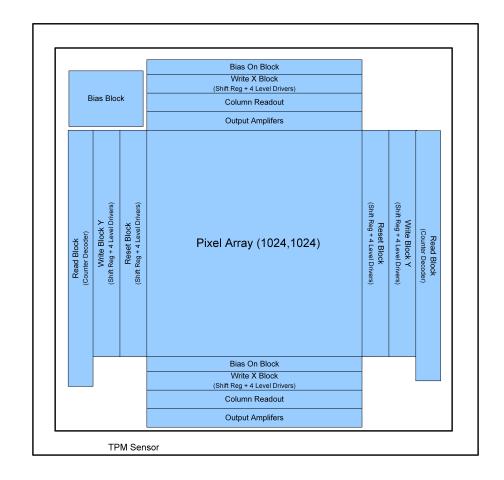
- The TPM pixel is based on a 3T-APS architecture with a partially pinned photodiode (PPPD).
- The pixel contains 8 transistors and a storage capacitor.
- It has 2 internal source-followers (SFs):
 - The 1st SF is used to drive the in-pixel storage node;
 - o The 2nd SF is used to drive the column readout node.
- In addition to that, it has 5 NMOS switches:
 - The RST switch is used to reset the photodiode node;
 - The BIASON switch is used to control the 1st SF;
 - o The SELECT switch is used to control the 2nd SF;
 - The WRITEX and WRITEY switches are used to implement a pre-defined grid pattern for TPM exposures.



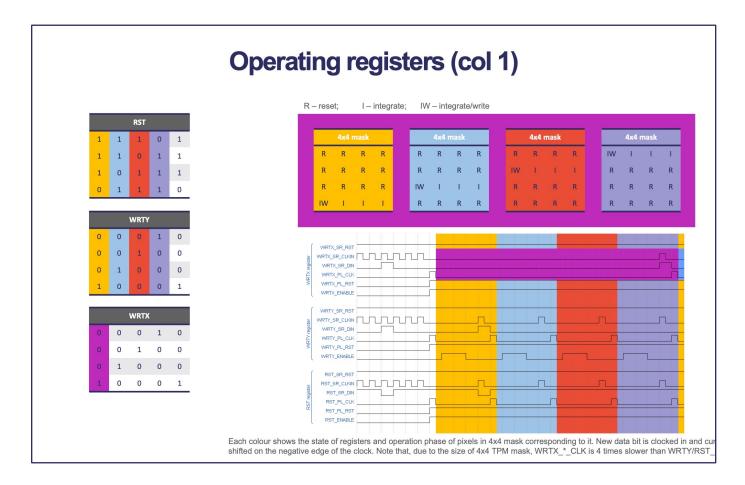


TPM sensor

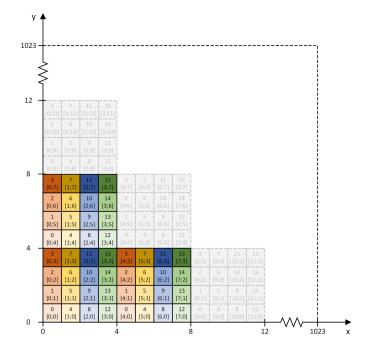
- The TPM pixel is controlled by RST, BIASON, WRITEX, WRITEY and SELECT signals.
- To reduce the load of the line, the control signals are split in the middle of the pixel array and driven from both sides:
 - The SELECT signal is controlled by a 10-bit counter placed on the left and right side of the chip;
 - The RST and WRITEY signals are controlled by two separate 1024bit shift registers placed on the left and right side of the chip;
 - The BIASON and WRITEX signals are controlled by two separate 1024-bit shift registers placed on top and bottom side of the chip.
- In case of a 4 × 4 TPM mask example, the pattern clocked through the BIASON, WRITEX and WRITEY shift registers should be 1000, whereas the pattern for the RST shift register should be 0111.
- The clock for WRITEX/BIASON shift registers should be 4 times slower than that for WRITEY/RST shift registers.







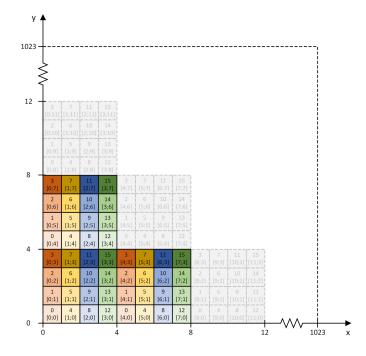
| 4x4 TPM mask | | | | | | | | |
|-----------------------|----------|-----------|----------|-----------|----------|-----------|----------|-----------|
| RST<3> → | 3 | | 7 | | 11 | | 15 | |
| WRTY<3> → | 3 | | | | 11 | | 13 | |
| RST<2> → | 2 | | 6 | | 10 | | 14 | |
| WRTY<2> → | | | 0 | | 10 | | 14 | |
| RST<1> → | 1 | | 5 | | 9 | | 13 | |
| WRTY<1> → | 1 | | 5 | | 9 | | 13 | |
| RST<0> → | 0 | | 4 | | 8 | | 12 | |
| WRTY<0> \rightarrow | U | | 4 | | ٥ | | 12 | |
| | ↑ | ↑ | 1 | 1 | ↑ | ↑ | ↑ | ↑ |
| | WRTX<0> | BIASON<0> | WRTX<1> | BIASON<1> | WRTX<2> | BIASON<2> | WRTX<3> | BIASON<3> |





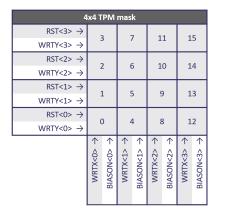


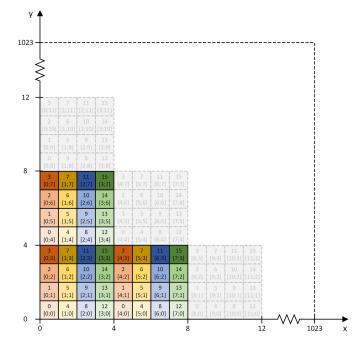
| 4x4 TPM mask | | | | | | | | |
|--------------|---------|-----------|---------|-----------|---------|-----------|---------|-----------|
| RST<3> → | 3 | | 7 | | 11 | | 15 | |
| WRTY<3> → | 3 | | | | 11 | | 15 | |
| RST<2> → | 2 | | 6 | | 10 | | 14 | |
| WRTY<2> → | | | | | | | | |
| RST<1> → | 1 | | 5 | | 9 | | 13 | |
| WRTY<1> → | 1 | | 5 | | 9 | | 13 | |
| RST<0> → | 0 | | 4 | | 8 | | 12 | |
| WRTY<0> → | U | | 4 | | 0 | | 12 | |
| | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 |
| | WRTX<0> | BIASON<0> | WRTX<1> | BIASON<1> | WRTX<2> | BIASON<2> | WRTX<3> | BIASON<3> |
| | Ę. | SON | Ę | SON | Ę | SON | Ę | SON |
| | > | BIA | > | BIA | > | BIA | > | BIA |
| | | | | | | | | |



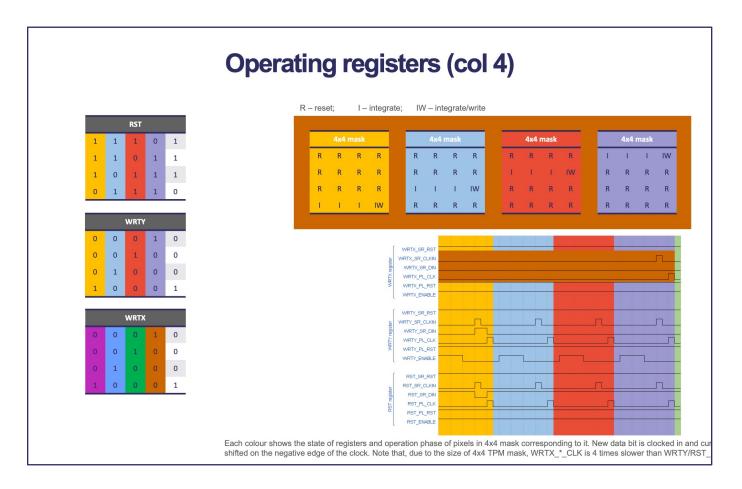




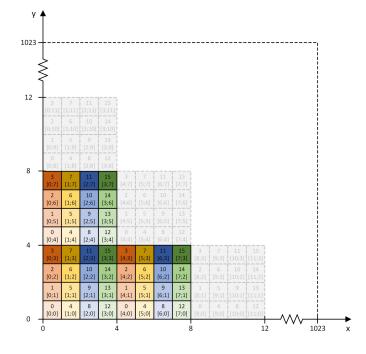






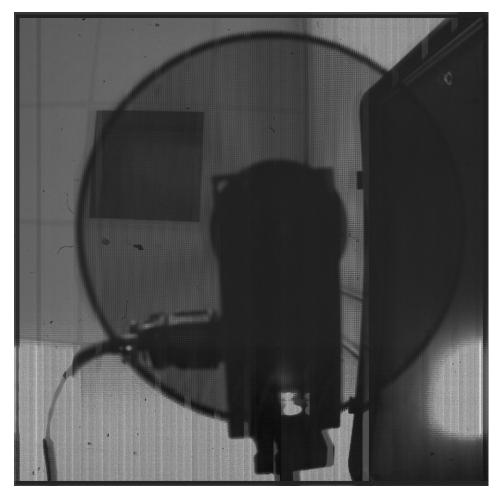


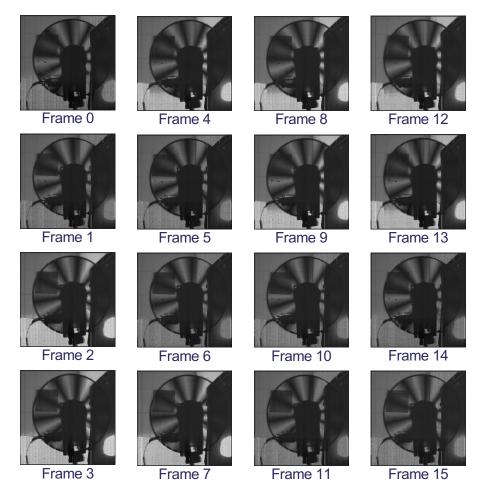
| 4x4 TPM mask | | | | | | | | |
|--------------|----------|-----------|----------|-----------|----------|-----------|----------|-----------|
| RST<3> → | 3 | | 7 | | 11 | | 15 | |
| WRTY<3> → | 3 | | | | 11 | | 15 | |
| RST<2> → | 2 | | 6 | | 10 | | 14 | |
| WRTY<2> → | 2 | | 0 | | 10 | | 14 | |
| RST<1> → | 1 | | 5 | | 9 | | 13 | |
| WRTY<1> → | 1 | | 5 | | 9 | | 13 | |
| RST<0> → | 0 | | 4 | | 8 | | 12 | |
| WRTY<0> → | U | | 4 | | 0 | | 12 | |
| | 1 | ↑ | 1 | ↑ | 1 | ^ | 1 | ↑ |
| | WRTX<0> | BIASON<0> | WRTX<1> | BIASON<1> | WRTX<2> | BIASON<2> | WRTX<3> | BIASON<3> |
| | M. L | SO | /RT | SO | VRT | SO | VRT | SOI |
| | > | BIA | > | BIA | > | BIA | > | BIA |
| | | | | | | | | |





TPM example with a 4 × 4 grid pattern







Summary

- Tower Semiconductor 180 nm 1.8/3.3 V CIS process technology
- High resolution: up to 1K × 1K
- Very high framing rate: up to 10 Mfps
- Configurable number of frames
- Analogue readout

| Parameter | Specifications | | | | | |
|--------------------------------|-----------------------|--|--|--|--|--|
| Pixel type | 8T with PPPD | | | | | |
| Floating diffusion capacitance | 5.6 fF | | | | | |
| Conversion gain | 17 μV/e ⁻ | | | | | |
| Maximum full-well capacity | ~52.5 ke- | | | | | |
| Fill factor | ~53% | | | | | |
| Pixel unit size | 10 μm × 10 μm | | | | | |
| Pixel array format | 1024 × 1024 | | | | | |
| Effective pixel array format | 1000 × 1000 | | | | | |
| Sensitive area | 10 mm × 10 mm | | | | | |
| Minimum integration time | 100 ns @ 10 MHz (TPM) | | | | | |
| Maximum output voltage swing | 1 V | | | | | |
| Maximum readout speed | 10 MS/s | | | | | |
| Readout frame rate | 300 fps | | | | | |







www.technologysi.stfc.ac.uk/Pages/CMOS-Sensors-Design.aspx

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Thankyou







